



SHEET 1 OF 1

FORM PTO - 1449				ATTY DOCKET NO.: ASC-023DVC2					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT: Fitzgerald					
				SERIAL NO.: 10/022,689					
				FILING DATE: December 17, 2001					
				GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
<i>12/</i>	A117	5,424,243	06/13/1995	Takasaki					
<i>12/</i>	A118	2002/0052084	05/02/2002	Fitzgerald			05/16/2001		
<i>12/</i>	A119	2003/0077867	04/24/2003	Fitzgerald			07/16/2001		
<i>12/</i>	A120	6,602,613	08/05/2003	Fitzgerald			01/17/2001		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
EXAMINER <i>Whitehead</i>					DATE CONSIDERED <i>2003</i>				

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FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110
Telephone: (617) 426-9180

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

MIT7759DIVCON
ATTORNEY DOCKET NO.

Eugene A. Fitzgerald
APPLICANT

Herewith
FILING DATE

Unknown
SERIAL NO.

Unknown
GROUP

Unknown
EXAMINER

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10/022689



U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
COY	AA	5,177,583	January 5, 1993	Endo et al.	257	190	January 10, 1991
	AB	5,298,452	March 29, 1994	Meyerson	437	81	February 21, 1992
	AC	5,630,905	May 20, 1997	Lynch et al.	438	507	June 5, 1995
	AD	5,906,951	May 25, 1999	Chu et al.	438	751	April 30, 1997
	AE	5,659,187	August 19, 1997	Legoues et al.	257	190	June 7, 1995
	AF	5,891,769	April 6, 1999	Liaw et al.	438	167	February 27, 1998
	AG	5,714,777	February 3, 1998	Ismail et al.	257	263	February 19, 1997
	AH	5,534,713	July 9, 1996	Ismail et al.	257	24	May 20, 1994
	AI	5,250,445	October 5, 1993	Bean et al.	437	11	January 17, 1992
	AJ	4,997,776	March 5, 1991	Haramé et al.	437	31	June 20, 1990
	AK	5,442,205	August 15, 1995	Brasen et al.			August 9, 1993
	AL	5,399,522	March 21, 1995	Ohuri			September 8, 1993
COY	AM	5,250,445	October 1993	Bean et al.	438	474	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
COY	AN	0 514 018 A2	16.04.92	EPO			
COY	AO	2 701 599	14.09.93	France			
	AP						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
COY	AQ	Currie et al., "Controlling Threading Dislocation in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing.; Vol. 72, No. 14, p. 1718-1720. February 1998.
EXAMINER	Whitehead	DATE CONSIDERED 2002
<p>EXAMINER: Initial if citati n considered, wh ther or not citation is in conformance with MPEP 609; draw lin through citation if n t in conformanc and not consid red. Include c py f this form with n xt communicati n t applicant.</p>		

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

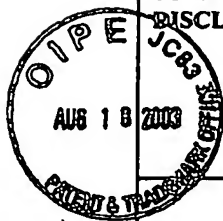
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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>lu</i>	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,710,788	12/01/1987	Dambkes et al.			
	A3	4,987,462	01/22/1991	Kim et al.			
	A4	4,990,979	02/05/1991	Otto			
	A5	5,013,681	05/07/1991	Godbey et al.			
	A6	5,155,571	10/13/1992	Wang et al.			
	A7	5,166,084	11/24/1992	Pfiester			
	A8	5,202,284	04/01/1993	Kamins et al.			
	A9	5,207,864	05/04/1993	Bhat et al.			
	A10	5,208,182	05/04/1993	Narayan et al.			
	A11	5,212,110	05/18/1993	Pfiester et al.			
	A12	5,221,413	06/22/1993	Brasen et al.			
	A13	5,241,197	08/31/1993	Murakami et al.			
	A14	5,285,086	02/08/1994	Fitzgerald, Jr.			
	A15	5,291,439	03/01/1994	Kauffmann, et al.			
	A16	5,310,451	05/10/1994	Tejwani et al.			
	A17	5,316,958	05/31/1994	Meyerson			
	A18	5,346,848	09/13/1994	Gruppen-Shemansky et al.			
	A19	5,374,564	12/20/1994	Bruel			
	A20	5,413,679	05/09/1995	Godbey			
	A21	5,426,069	06/20/1995	Selvakumar et al.			
	A22	5,426,316	06/20/1995	Mohammad			
	A23	5,461,243	10/24/1995	Ek et al.			
	A24	5,461,250	10/24/1995	Burghartz et al.			
	A25	5,462,883	10/31/1995	Dennard et al.			
	A26	5,476,813	12/19/1995	Naruse			
	A27	5,479,033	12/26/1995	Baca et al.			
	A28	5,484,664	01/16/1996	Kitahara et al.			
	A29	5,523,243	06/04/1996	Mohammad			
<i>lu</i>	A30	5,523,592	06/04/1996	Nakagawa et al.			


EXAMINER

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U.S. PATENT DOCUMENTS							
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<div style="font-size: 2em; transform: rotate(-90deg); display: inline-block;"> 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 </div>	A31	5,536,361	07/16/1996	Kondo et al.			
	A32	5,540,785	07/30/1996	Dennard et al.			
	A33	5,596,527	01/12/1997	Tomioka, et al.			
	A34	5,617,351	04/01/1997	Bertin, et al.			
	A35	5,683,934	11/04/1997	Candelaria			
	A36	5,698,869	12/16/1997	Yoshimi et al.			
	A37	5,728,623	03/17/1998	Mori			
	A38	5,739,567	04/14/1998	Wong			
	A39	5,759,898	06/02/1998	Ek et al.			
	A40	5,777,347	07/07/1998	Bartelink			
	A41	5,786,612	07/28/1998	Otani et al.			
	A42	5,786,614	07/28/1998	Chuang, et al.			
	A43	5,792,679	08/11/1998	Nakato			
	A44	5,808,344	09/15/1998	Ismail et al.			
	A45	5,847,419	12/08/1998	Imai et al.			
	A46	5,877,070	03/02/1999	Goesele et al.			
	A47	5,906,708	05/25/1999	Robinson et al.			
	A48	5,912,479	06/15/1999	Mori et al.			
	A49	5,943,560	08/24/1999	Chang et al.			
	A50	5,963,817	10/05/1999	Chu et al.			
	A51	5,966,622	10/12/1999	Levine et al.			
	A52	5,998,807	12/07/1999	Lustig et al.			
	A53	6,013,134	01/11/2000	Chu et al.			
	A54	6,033,974	03/07/2000	Henley et al.			
	A55	6,033,995	03/07/2000	Muller			
	A56	6,058,044	05/02/2000	Sugiura et al.			
	A57	6,074,919	06/13/2000	Gardner et al.			
	A58	6,096,590	08/01/2000	Chan et al.			
	A59	6,103,559	08/15/2000	Gardner et al.			
	A60	6,111,267	08/29/2000	Fischer et al.			

EXAMINER <i>Heena Schulz</i>	DATE CONSIDERED <i>8/4/04</i>
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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>RL</i>	A61	6,117,750	09/12/2000	Bensahel et al.			
	A62	6,130,453	10/10/2000	Mei, et al.			
	A63	6,133,799	10/17/2000	Favors, Jr., et al.			
	A64	6,140,687	10/31/2000	Shimomura et al.			
	A65	6,143,636	11/07/2000	Forbes, et al.			
	A66	6,153,495	11/28/2000	Kub et al.			
	A67	6,154,475	11/28/2000	Soref et al.			
	A68	6,160,303	12/12/2000	Fattaruso			
	A69	6,162,688	12/19/2000	Gardner et al.			
	A70	6,184,111	02/06/2001	Henley et al.			
	A71	6,191,007	02/20/2001	Matsui et al.			
	A72	6,191,432	02/20/2001	Sugiyama et al.			
	A73	6,194,722	02/27/2001	Fiorini et al.			
	A74	6,204,529	03/20/2001	Lung, et al.			
	A75	6,207,977	03/01/2001	Augusto			
	A76	6,210,988	04/03/2001	Howe et al.			
	A77	6,218,677	04/17/2001	Broekaert			
	A78	6,232,138	05/15/2001	Fitzgerald et al.			
	A79	6,235,567	05/22/2001	Huang			
	A80	6,242,324	06/05/2001	Kub et al.			
	A81	6,249,022	06/19/2001	Lin, et al.			
	A82	6,251,755	06/26/2001	Furukawa et al.			
	A83	6,261,929	07/01/2001	Gehrke et al.			
	A84	6,266,278	07/24/2001	Harari, et al.			
	A85	6,271,551	08/07/2001	Schmitz et al.			
	A86	6,271,726	08/07/2001	Fransis et al.			
	A87	6,313,016	11/06/2001	Kibbel et al.			
	A88	6,316,301	11/13/2001	Kant			
	A89	6,323,108	11/27/2001	Kub et al.			
<i>RL</i>	A90	6,329,063	12/11/2001	Lo et al.			

EXAMINER <i>Norma Schulz</i>	DATE CONSIDERED <i>8/4/04</i>
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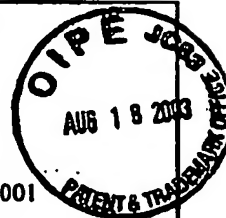


U.S. PATENT DOCUMENTS

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<i>RL</i>	A91	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A92	6,339,232	01/15/2002	Takagi			09/20/1999
	A93	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A94	6,372,356	04/16/2002	Thornton et al.			04/028/2000
	A95	6,399,970	06/04/2002	Kubo et al.			09/16/1997
	A96	6,407,406	06/18/2002	Tezuka			06/29/1999
	A97	6,425,951	07/30/2002	Chu et al.			08/06/1999
	A98	6,429,061	08/06/2002	Rim			07/26/2000
	A99	6,420,937	07/16/2002	Akatsuka et al.			06/14/2001
	A100	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A101	6,555,839	04/29/2003	Fitzgerald			05/16/2001
	A102	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A103	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A104	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
	A105	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
	A106	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A107	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A108	2002/0096717	07/25/2002	Chu et al.			01/25/2001
	A109	2002/0100942	08/01/2001	Fitzgerald et al.			06/19/2001
	A110	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A111	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
	A112	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A113	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A114	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A115	6,603,156	08/05/2003	Rim			03/31/2001
<i>RL</i>	A116	2003/0003679	01/02/2003	Doyle et al.			06/29/2001

EXAMINER	<i>Wesley Schult</i>	DATE CONSIDERED	<i>8/4/04</i>
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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTY DOCKET NO.:	ASC-023DVC2
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FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				NO	NO
	B2	0 587 520	03/16/1994	EP				NO	YES
	B3	0 683 522	11/22/1995	EP				NO	YES
	B4	0 828 296	03/11/1998	EP				NO	YES
	B5	0 829 908	03/18/1998	EP				NO	YES
	B6	0 838 858	04/29/1998	EP				NO	NO
	B7	1 020 900	07/19/2000	EP				NO	YES
	B8	1 174 928	01/23/2002	EP				NO	YES
	B9	2 342 777	04/19/2000	GB				YES	YES
	B10	10-270685	10/09/1998	JP				NO	YES
	B11	11-233744	08/27/1999	JP				NO	NO
	B12	2000-021783	08/31/2000	JP				NO	YES
	B13	2000-031491	01/28/2000	JP				NO	NO
	B14	2001-319935	11/16/2001	JP				NO	YES
	B15	2002-076334	03/15/2002	JP				NO	YES
	B16	2002-164520	06/07/2002	JP				NO	YES
	B17	2002-289533	10/04/2002	JP				NO	YES
	B18	4-307974	10/30/1992	JP				NO	NO
	B19	5-166724	07/02/1993	JP				NO	Abstract Only
	B20	6-177046	06/24/1994	JP				NO	Abstract Only
	B21	7-106446	04/21/1995	JP				NO	NO
	B22	7-240372	09/12/1995	JP				NO	Abstract Only
	B23	00/48239	08/17/2000	WO				NO	YES
	B24	00/54338	09/14/2000	WO				NO	YES


EXAMINER	<i>hanna schultz</i>	DATE CONSIDERED	<i>8/4/04</i>
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
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	B26	01/54202	07/26/2001	WO				NO	YES
	B27	01/93338	12/06/2001	WO				NO	YES
	B28	01/99169	12/27/2001	WO				NO	YES
	B29	02/071488	09/12/2002	WO				NO	YES
	B30	02/071491	09/12/2002	WO				NO	YES
	B31	02/071495	09/12/2002	WO				NO	YES
	B32	02/082514	10/17/2002	WO				NO	YES
	B33	02/13262	02/14/2002	WO				NO	YES
	B34	02/15244	02/21/2002	WO				NO	YES
	B35	02/27783	04/04/2002	WO				NO	YES
	B36	02/47168	06/13/2002	WO				NO	YES
	B37	98/59365	12/30/1998	WO				NO	YES
	B38	99/53539	10/21/1999	WO				NO	YES
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EXAMINER <i>Harold Schuy</i>	DATE CONSIDERED <i>8/4/04</i>
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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
[Signature]	C1	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting) pp. 761-764.
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.
	C3	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997).
	C4	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," Modern Physics Letters B (2001) (abstract).
	C5	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999) pp. 205-210.
	C6	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 µm bulk CMOS Experimental study," IEEE, (1996) pp. 21.2.1-21.2.4.
	C7	Bruel et al., "QSMART CUT: A Promising New SOI Material Technology," Proceedings 1995 IEEE International SOI Conference (October 1995) pp. 178-179.
	C8	Bruel, "Silicon on Insulator Material Technology," Electronic Letters, Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.
	C9	Bufler et al., "Hole transport in strained Si1-xGex alloys on Si1-yGe y substrates," Journal of Applied Physics, Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
	C10	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 1, January 1996, pp. 100-104.
	C11	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002) (abstract).
	C12	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," IEEE (2000) pp. 1006-1011
	C13	Chang et al., "Selective Etching of SiGe/Si Heterostructures," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 202-204.
	C14	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," IEEE Electron Device Letters, Vol. 22, No. 7 (July 2001) pp. 321-323.
[Signature]	C15	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," Journal of Electronic Materials, Vol. 30, No. 12 (2001) pp. L37-L39.

EXAMINER <i>Heena Singh</i>	DATE CONSIDERED <i>8/4/04</i>
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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>Kh</i>	C16	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," Journal of Vacuum Science and Technology A, Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.
	C17	Currie et al., "Carrier mobilities and process stability of strained S in- and p-MOSFETs on SiGe virtual substrates," J. Vac. Sci. Technol. B., Vol. 19, No. 6 (Nov/Dec 2001) pp. 2268-2279.
	C18	Eaglesham et al., "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," Physical Review Letters, Vol. 64, No. 16 (April 16, 1990) pp. 1943-1946.
	C19	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," Journal of Electronic Materials, Vol. 23, No. 6 (June 1994) pp. 493-496.
	C20	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," J. Appl. Phys., Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.
	C21	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," Journal of Applied Physics, Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.
	C22	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," Materials Science and Engineering B67, (1999) pp. 53-61.
	C23	Fitzgerald et al., "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) American Vacuum Society, pp. 1807-1819
	C24	Fitzgerald et al., "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," Applied Physics Letters, Vol. 59, No. 7 (August 12, 1991) pp. 811-813.
	C25	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," Applied Physics Letters, Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.
	C26	Gray and Meyer, "Analysis and Design of Analog Integrated Circuits", John Wiley & Sons, 1984, pp. 605-632.
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EXAMINER <i>hanna schutz</i>	DATE CONSIDERED <i>8/4/04</i>
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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTY DOCKET NO.:	ASC-023DVC2
	APPLICANTS:	Fitzgerald
	SERIAL NO.:	10/022,689
	FILING DATE:	December 17, 2001
	GROUP:	2813



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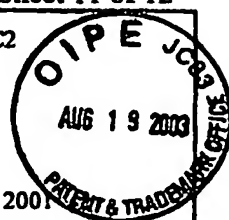
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Nancy Schuff

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EXAMINER <i>Laura Schuff</i>	DATE CONSIDERED <i>8/4/04</i>
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EXAMINER <i>Karen Schutz</i>	DATE CONSIDERED <i>8/4/04</i>
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				GROUP: 2813					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
<i>JS</i>	A117	5,424,243	06/13/1995	Takasaki					
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<i>JS</i>	A120	6,602,613	08/05/2003	Fitzgerald			01/17/2001		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
EXAMINER <i>Wesley Scholz</i>					DATE CONSIDERED <i>3/13/07</i>				

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